

Epi - Wafer

Undoped GaN



Feature	Undoped GaN Epi. Wafer Single side polished (Growth surface)
Diameter	2" (50.8mm)
Thickness (Included substrate)	430 μ m \pm 15 μ m
Structure	u-GaN / Sapphire substrate



GaN on Sapphire Wafer

Characteristics (at 25°C)

Parameter		Typ.	Test Conditions
PL measurement	Peak wavelength	364nm \pm 1nm	Etamax PLATO - Laser : 213nm
	Uniformity STD	<3%	
	FWHM	<10nm	
	FWHM STD	<3%	
Thickness	Thickness	2 μ m \pm 10%	
	Thickness STD	<10%	
XRD	(002)	<350 arcsec	Panalytical HRXRD
	(102)	<450 arcsec	
Hall	Carrier Concentration	< -1×10^{17} /cm	Accent HL5500
	Mobility	>200 cm ² /V-sec	
Doping material	Si	N/A	-
	Mg	N/A	

Normalized Single Spectrum(300 ~ 700nm)

